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# **Resistivity and magnetoresistance studies on RCoGe<sub>3</sub>** (**R** = La, Ce) compounds

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**Abstract.** Resistivity ( $\rho$ ) and magnetoresistance ( $\Delta \rho / \rho(0)$ ) have been measured for polycrystalline LaCoGe<sub>3</sub> and CeCoGe<sub>3</sub> compounds. The temperature dependence of  $\rho$  for the La compound is described by  $\rho \propto T^3$  for  $T \ll \vartheta_D$  and  $\propto T$  at high temperatures. At 4.5 K a significantly large  $\Delta \rho / \rho(0)(\sim 1)$  is observed. In CeCoGe<sub>3</sub>  $\rho(T)$  exhibits a sharp drop below the magnetic ordering temperature, 21 K. In the antiferromagnetic region between 4 and 16 K it follows a quadratic temperature dependence. The magnetic contribution to resistivity,  $\rho_m$ , exhibits a maximum at ~125 K above which it decreases following a logarithmic temperature dependence. The magnetoresistance remains positive for temperatures between 4.5 and 30 K but shows field induced transitions at ~7 kOe and ~28 kOe.

## 1. Introduction

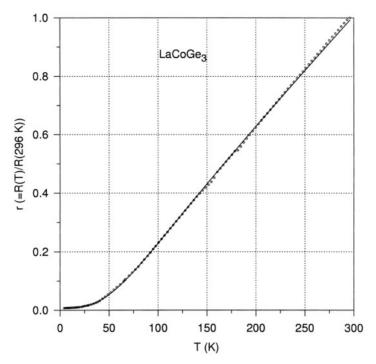
Tetragonal systems with ThCr<sub>2</sub>Si<sub>2</sub> structure have been a subject of extensive investigation [1]. Compounds with similar structure but of lower symmetry, i.e. BaNiSn<sub>3</sub>-type structure also are found to exhibit a wide variety of behaviour but are less studied. CeFeGe<sub>3</sub> is a non-magnetic compound with high Kondo temperature [2]. CeNiGe<sub>3</sub> exhibits magnetic ordering below 4.2 K [3]. CeCoSi<sub>3</sub> is a superconductor with  $T_C \sim 1.4$  K [4]. CeCoGe<sub>3</sub> is reported be a heavy fermion system and also exhibits complex temperature and field induced magnetic behaviour below 21 K [5]. To shed more light on the various magnetic phases we have carried out resistivity and magnetoresistance measurements on LaCoGe<sub>3</sub> and CeCoGe<sub>3</sub>, the results of which are reported here.

## 2. Experimental details

The samples were prepared by arc melting the stoichiometric amounts of the constituent elements in Ti-gettered argon atmosphere. The buttons were then chill cast drawn in the form of rods for transport measurements. These were sealed in an evacuated quartz tube and annealed at 800 °C for one week. X-ray powder diffraction measurements reveal them to be single phase with a BaNiSn<sub>3</sub>-type structure (space group *I4mm*). The tetragonal cell parameters calculated using a least squares fit method are a = 4.346 Å and c = 9.870 Å

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**Figure 1.** The temperature dependence of normalized resistance, r(= R(T)/R(296 K)) of LaCoGe<sub>3</sub>. The continuous line is the fit to the equation discussed in the text.

for LaCoGe<sub>3</sub> and a = 4.314 Å and c = 9.815 Å for CeCoGe<sub>3</sub>, in agreement with reported values [5]. Dc resistivity and magnetoresistance measurements were measured using a standard four-probe method.

## 3. Results and discussion

#### 3.1. $LaCoGe_3$

The value of  $\rho(296 \text{ K})$  is 57  $\mu\Omega$  cm and the residual resistivity ratio (RRR), R(296 K)/R(4.2 K) is found to be 150. The variation of normalized resistance, r(=R(T)/R(296 K)) as a function of temperature is shown in figure 1. The temperature dependence of r exhibits a normal metallic behaviour as the temperature is reduced. It does not exhibit either magnetic or superconducting transition down to 4.2 K. The value of  $\rho(296 \text{ K})$  is nearly half the reported value of  $\sim 100 \,\mu\Omega$  cm in LaCoSi<sub>3</sub> with similar structure [4]. This large value of RRR for a polycrystalline sample suggests a very ordered system. The temperature dependence of the resistivity could not be fitted to a Bloch–Grüneisen relation where for  $T \ll \theta_D$ ,  $\rho \propto T^5$ . Instead in the region between 4.2 and 300 K the temperature dependence of the resistivity could be fitted to an expression of the form

$$\rho(T) = \rho(0) + c_1 \left(\frac{T}{\theta_D}\right)^3 \int_0^{\theta_D/T} \frac{x^3 \, \mathrm{d}x}{(1 - \mathrm{e}^{-x})(\mathrm{e}^x - 1)^3}$$

where  $\rho(0)$  is the residual resistivity, the second term is due to the electron–phonon scattering and  $\theta_D$  is the Debye temperature. The continuous line through the data points in figure 1 indicate the fitted line. The fit holds good except for the region T > 250 K where differences

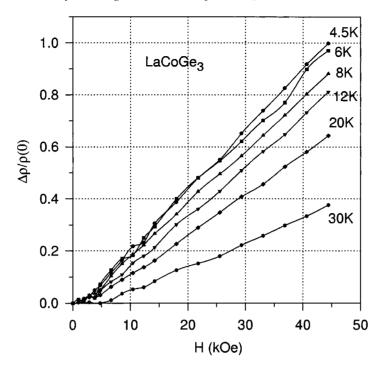


Figure 2. The magnetic field dependence of the magnetoresistance of  $LaCoGe_3$  at various temperatures.

appear between the fitted and observed values. For  $T \ll \theta_D$ ,  $\rho \propto T^3$ . This form of temperature dependence has also been observed in the case of La<sub>2</sub>Rh<sub>3</sub>Si<sub>5</sub> [6] and attributed to Wilson's s–d scattering model.  $\theta_D$  has been used as a parameter. The value of  $\theta_D$  (= 360 K) obtained from the fit is in good agreement with that obtained from independent specific heat measurements [5]. Its value is larger than that reported (=298 K) in the case of LaFeGe<sub>3</sub> [2].

The magnetoresistance MR,  $\Delta \rho / \rho(0) (= [\rho(H) - \rho(0)] / \rho(0))$  as a function of magnetic field at various temperatures is shown in figure 2. It is positive at all temperatures between 4.2 and 30 K and its magnitude at a given field decreases with increase in temperature. It varies nearly linearly with field at all temperatures. The magnitude of MR at 4.2 K and 45 kOe is almost 1.0. This denotes a significantly large value for a polycrystalline sample. In comparison for LaCu<sub>6</sub>  $\Delta \rho / \rho(0)$  is only ~0.11 at a similar temperature and field [7]. The large value for  $\Delta \rho / \rho(0)$  could possibly be due to the low value of  $\rho(4.2 \text{ K})$ . It is found that the temperature dependence of MR is in agreement with the Kohler law i.e.  $\Delta \rho / \rho(0) = f(H / \rho(0))$ . In figure 3 we show the plot of  $\Delta \rho / \rho(0)$  against  $H / \rho(0)$ . It is observed that all the data points between 4.2 and 30 K fall on a single curve. The validity of Kohler's plot over a wide temperature range indicates the absence of spin dependent scattering.

# 3.2. CeCoGe<sub>3</sub>

The resistivity  $\rho$ , of CeCoGe<sub>3</sub> at 300 K is 127  $\mu\Omega$  cm and RRR ~30. The temperature variation of resistivity is shown in figure 4. The resistivity decreases as the temperature is lowered. However, the variation in  $\rho$  between 300 and 150 K is only ~15  $\mu\Omega$  cm as compared to a large decrease of ~100  $\mu\Omega$  cm below 100 K. There is a marked change in the behaviour of  $\rho$  at ~21 K

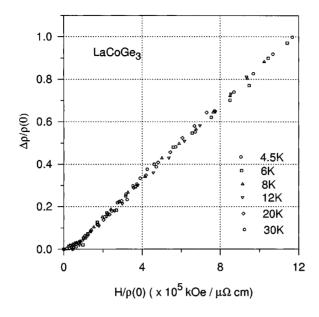
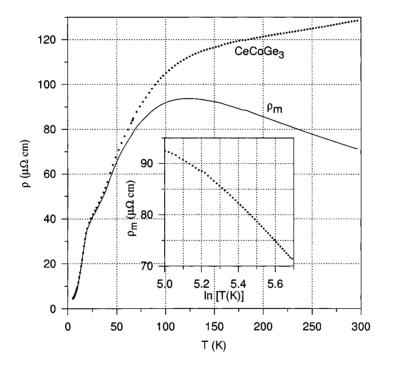
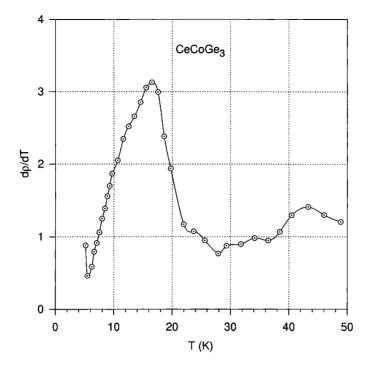


Figure 3. The magnetoresistance as a function of  $H/\rho(0)$  of LaCoGe<sub>3</sub> at various temperatures.



**Figure 4.** The temperature dependence of resistivity of CeCoGe<sub>3</sub> and  $\rho_m$  (= $\rho$ (CeCoGe<sub>3</sub>)  $-\rho$ (LaCoGe<sub>3</sub>)). The inset shows the logarithmic temperature variation of  $\rho_m$ .

indicating the transition to a magnetically ordered state below this temperature. The behaviour of  $d\rho/dT$  (figure 5) gives a better picture. It exhibits a maximum at 16.5 K and is identified with the antiferromagnetic transition. This is in agreement with the reported magnetic phase diagram



**Figure 5.** The temperature variation of  $d\rho/dT$  of CeCoGe<sub>3</sub>.

[5], where it is proposed that the system in zero magnetic field undergoes a paramagnetic to a ferrimagnetic transition at 21 K and subsequently to an antiferromagnetic phase below 16 K. However, from the derivative plot the para to ferrimagnetic transition is not very clear:  $d\rho/dT$ continuously increases below 22 K. It needs to be pointed out that no negative  $d\rho/dT$  in the temperature region around the ordering temperature, 16.5 K is observed. Normally the onset of commensurate antiferromagnetic order is associated with an increase in  $\rho$  due to the magnetic superzone gap effect [8, 9], which results in negative  $d\rho/dT$  at the  $T_N$ . Its absence here could be a result of either the formation of intervening ferrimagnetic state between para and AF or the absence of the gap itself. Below  $T_N$ ,  $d\rho/dT$  steadily decreases due to the increase in AF order. Between 4.5 and 16 K  $\rho(T)$  exhibits a quadratic temperature dependence of the form  $\rho(T) = \rho(0) + AT^2$  where  $\rho(0) = 1 \ \mu\Omega$  cm and  $A = 0.096 \ \mu\Omega$  cm K<sup>-2</sup>. The value of A is of the same magnitude as reported in the case of  $\alpha$ -Mn,  $A = 0.11 \ \mu\Omega$  cm K<sup>-2</sup> [10]. The larger value of  $\rho(0)$  as compared to LaCoGe<sub>3</sub> is attributed to the contribution from antiferromagnetic coupling of magnetic moments. For T > 21 K the difference in the variation of  $\rho$  between the normal metallic behaviour in LaCoGe<sub>3</sub> and CeCoGe<sub>3</sub> is attributed to the magnetic contribution to  $\rho$  in CeCoGe<sub>3</sub>. Assuming that the phonon contribution is similar in both the compounds we estimate the magnetic contribution to  $\rho$  in CeCoGe<sub>3</sub>,  $\rho_m (= \rho (CeCoGe_3) - \rho (LaCoGe_3))$ .  $\rho_m$ exhibits a broad maximum at  $\sim 125$  K above which it decreases. It follows a  $- \ln T$  behaviour for T > 170 K (shown in the inset of figure 4). The earlier report of resistivity studies on this compound shows a linear variation of R(T) for 21 K < T < 100 K [5]. Our results clearly show the highly non-linear behaviour of  $\rho$  above the magnetic ordering temperature. The maximum in  $\rho_m$  at 125 K is understood to be a result of the Kondo effect influenced by crystal field effects as discussed by Cornut and Coqblin [11]. The temperature at which  $\rho_m$ is a maximum is an indication of the energy difference between the crystal field split energy

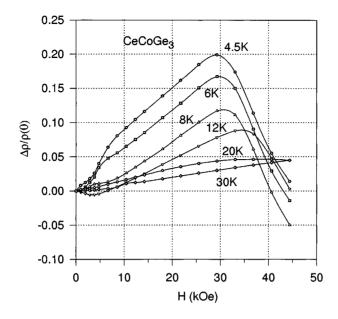


Figure 6. The magnetic field variation of magnetoresistance of CeCoGe<sub>3</sub> at various temperatures.

levels. Our observations indicate that the lowest excited crystal field level is ~100 K and the value is of the same order as deduced from zero-field heat capacity results [5]. It is of interest to note that the high temperature resistivity behaviours are similar in the case of CeFeGe<sub>3</sub> [2], CeNiGe<sub>3</sub> [3] and the present compound, irrespective of the ground state. The maximum in  $\rho_m$  occurs at ~100 K suggesting similar CEF splitting in these compounds.

The variation of  $\Delta \rho / \rho(0)$  with magnetic field at various temperatures is shown in figure 6. It is positive for all temperatures between 4.2 and 30 K but shows two field induced transitions. The first transition at  $H \sim 7$  kOe results in increase in resistance whereas the second transition at  $H \sim 28$  kOe is accompanied by a significant decrease in resistance (~0.20). Knowing the magnetic phase diagram [5] the various transitions are identified with three distinct regions. For H < 7 kOe in the antiferromagnetic state  $\Delta \rho / \rho(0)$  varies as  $H^n$  with n > 1. As temperature is increased this transition disappears rapidly. Between 10 and 28 kOe the variation is nearly linear in the state where the magnetic state is a mixture of AF and ferrimagnetic. For H > 29 kOe the slope of  $\Delta \rho / \rho(0)$  changes from positive to negative indicating the transition to a ferromagnetic state. The field,  $H_m$  at which the maximum in  $\Delta \rho / \rho(0)$  occurs shifts to higher fields as the temperature is increased from 4.2 to 12 K. The observed behaviour of the shift of  $H_m$  to higher field as temperature is increased is similar to that reported from the magnetization measurements [5]. This is different from similar metamagnetic behaviour observed in CeRh<sub>2</sub>Ge<sub>2</sub> where the field  $H_m$  is found to shift to lower fields as the transition temperature is approached [12].

## 4. Conclusions

The temperature dependence of resistivity for LaCoGe<sub>3</sub> is described by  $\rho \propto T^3$  for  $T \ll \vartheta_D$ and  $\propto T$  at high temperatures. The magnetoresistance  $\Delta \rho / \rho(0)$  at 4.5 K exhibits larger values than at higher temperatures and follows Kohler's law indicating the absence of spin dependent scattering. For CeCoGe<sub>3</sub>,  $\rho(T)$  exhibits a magnetic ordering below 21 K. Below the ordering temperature a quadratic temperature dependence is followed. The magnetic contribution to resistivity,  $\rho_m$  exhibits a maximum at ~125 K above which it follows a  $-\ln T$  behaviour indicating the influence of crystal fields on the Kondo effect. The variation of  $\Delta \rho / \rho(0)$  as a function of *H* indicates transitions at 7 and 28 kOe.

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